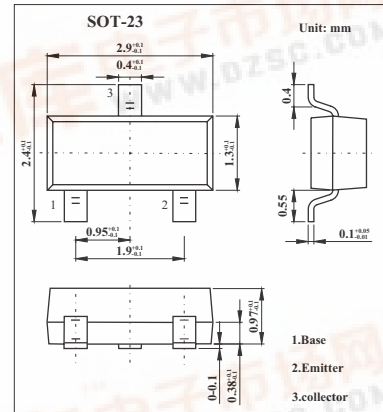


SMD Type Transistors

Silicon PNP Epitaxial Planar Type  
2SC2404

■ Features

- Optimum for RF amplification of FM/AM radios
- High transition frequency  $f_T$
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	30	V
Collector-emitter voltage	$V_{CE0}$	20	V
Emitter-base voltage	$V_{EB0}$	3	V
Collector current	$I_C$	15	mA
Collector power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	$V_{CB0}$	$I_C = 10 \mu\text{A}, I_E = 0$	30			V
Emitter-base voltage	$V_{EB0}$	$I_E = 10 \mu\text{A}, I_C = 0$	3			V
Base-emitter voltage	$V_{BE}$	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}$		0.72		V
Forward current transfer ratio	$h_{FE}$	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}$	65		260	
Transition frequency	$f_T$	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$	450	650		MHz
Reverse transfer capacitance	$C_{re}$	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 10.7 \text{ MHz}$		0.8	1.0	pF
Power gain	$G_P$	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$		24		dB
Noise figure	NF	$V_{CB} = 6 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$		3.3		dB

■  $h_{FE}$  Classification

Marking	U	
	C	D
$h_{FE}$	65~160	100~260

